3. (Amended) A method of forming a light emitting device, said method comprising:

forming at least one of Fresnel lens and holographic diffuser on at least one surface of a semiconductor light emitter to affect light emitted by said semiconductor light emitter;

wherein said forming comprises pressing a stamping block against at least one surface of said semiconductor light emitter.

4. (Amended) The method of claim 3 wherein said forming is executed concurrently with a wafer-bonding process, said wafer-bonding process comprising:

removing a first substrate of said semiconductor light emitter; and

bonding a second substrate to said semiconductor light emitter.

5. (Amended) A method of forming a light emitting device, said method comprising:

forming at least one of Fresnel lens and holographic diffuser on at least one surface of a semiconductor light emitter to affect light emitted by said semiconductor light emitter;

wherein said forming comprises at least one method selected from ablation, machining, scribing, electron discharge machining, and stamping.

8. (Amended) The method of claim 1 wherein said semiconductor light emitter has a light emitting layer, the method further comprising confining light emission to a preselected section of said light emitting layer, wherein said confining comprises at least one method selected from applying the Holonyak process, using selective area growth, using selective area bonding, using diffusion, and using ion implantation.

9. (Amended) The method of claim 3 further comprising:

coating one or more surfaces of said semiconductor light emitter with a reflective material.

10. (Amended) The method of claim 3 further comprising:

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coating said Fresnel lens or said holographic diffuser with a reflective material.

11. The method of claim 2 further comprising:

forming an optical element on the surface opposite of said extraction surface.

12. (Amended) A light emitting device comprising:

a semiconductor light emitter; and

a first optical element stamped on at least one surface of said semiconductor light emitter, said first optical element comprising one of Fresnel lens and holographic diffuser.

13. The device of claim 12 further comprising:

a reflective material coating at least one surface of said device.

23. The device of claim 12, wherein said first optical element is designed to achieve one of light focusing, light collimating, and light diverging.

24. The device of claim 12 wherein said first optical element is designed to direct light in a preselected direction.

27. A method of forming a light emitting device, said method comprising:

stamping at least one optical element on at least one surface of a semiconductor light emitter to affect the light emitted by said semiconductor light emitter.

28. The method of claim 27 further comprising:

coating a surface of said light emitting device with a reflective layer.

29. The method of claim 27 wherein said stamping is done on at least one of a semiconductor layer and a substrate layer of said semiconductor light emitter.

30. The method of claim 29 wherein said semiconductor layer comprises a transparent aluminum-bearing compound.

31. The method of claim 27, wherein said stamping is executed at an elevated temperature, said elevated temperature being higher than room temperature.

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32. The method of claim 31, further comprising lowering said elevated temperature to facilitate the separation of a stamping block from said semiconductor light emitter after said stamping.

33. The method of claim 32, wherein said elevated temperature is higher than the ductile transition temperature of the material constituting said at least one surface on which said optical element is formed.

34. A light emitting device comprising:

a semiconductor light emitter; and

at least one optical element stamped on at least one surface of said semiconductor light emitter, wherein said optical element is a first optical element.

41. (Amended) A light emitting diode array comprising a plurality of light emitting devices, a light emitting device comprising:

a semiconductor light emitter; and

one of a Fresnel lens and a holographic diffuser stamped on a surface of said semiconductor light emitter.

42. A light emitting array comprising a plurality of light emitting devices, a light emitting device comprising:

a semiconductor light emitter; and

an optical element stamped on a surface of said semiconductor light emitter.

43. (Amended) A display device comprising at least one blue light emitting device, at least one green light emitting device, and at least one red light emitting device, wherein at least one of said blue light emitting device, green light emitting device, and red light emitting device comprises:

a semiconductor light emitter; and

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one of a Fresnel lens and a holographic diffuser [formed] stamped on a surface of said semiconductor light emitter.

44. A display device comprising at least one blue light emitting device, at least one green light emitting device, and at least one red light emitting device, wherein at least one of said blue light emitting device, green light emitting device, and red light emitting device comprises:

a semiconductor light emitter; and

one optical element stamped on a surface of said semiconductor light emitter.

45. (Twice Amended) A method for forming a light emitting device, said method comprising:

stamping an optical element in a material, said material being transparent to light emitted from said light emitting device, said material being one of high index optical glass, III-V semiconductors, II-VI semiconductors, group IV semiconductors, high-index organic semiconductors, high index organic compounds, and mixtures or alloys thereof; and

bonding said material to a semiconductor light emitter.

46. The method of Claim 45, wherein said stamping precedes said bonding.

47. The method of Claim 45, wherein said bonding precedes said stamping.

Please add the following new claims:

50. (New) The method of Claim 45, wherein bonding comprises bonding said material to a semiconductor light emitter with a bonding material, said bonding material being one of high index optical glass, III-V semiconductors, II-VI semiconductors, group IV semiconductors, high-index organic semiconductors, high index organic compounds, and mixtures or alloys thereof.

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51. (New) The method of Claim 45, wherein bonding comprises pressing said material together with said semiconductor light emitter at a temperature greater than room temperature.

52. (New) A light emitting device comprising:

a semiconductor light emitter; and

an optical element stamped on a material transparent to light emitted from said light emitting device, said material being one of high index optical glass, III-V semiconductors, II-VI semiconductors, group IV semiconductors, high-index organic semiconductors, high index organic compounds, and mixtures or alloys thereof;

wherein said material is bonded to said semiconductor light emitter.

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